

What is claimed is:

1. A **[crystal] quartz** thin film made by depositing at least one silicon alkoxide selected from the group consisting of tetramethoxysilane, tetraethoxysilane, tetrapropoxysilane and tetrabutoxysilane on a substrate under atmospheric pressure.

2. A **[crystal] quartz** thin film as claimed in claim 1, which is a **[crystal] quartz** epitaxial thin film.